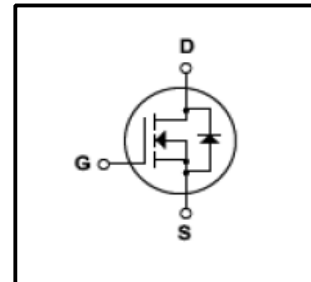
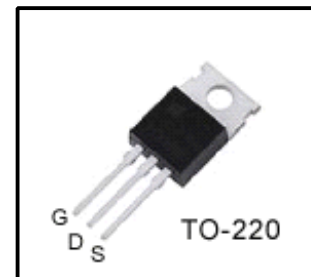


Silicon N-Channel MOSFET
Features

- 18A,500V, $R_{DS(on)}$ (Max0.27 Ω)@ $V_{GS}=10V$
- Ultra-low Gate charge(Typical 42nC)
- Fast Switching Capability
- 100%Avalanche Tested
- Maximum Junction Temperature Range(150℃)


General Description

This Power MOSFET is produced using Winsemi's advanced planar stripe, VDMOS technology. This latest technology has been especially designed to minimize on-state resistance, have a high rugged avalanche characteristics. This device is specially well suited for AC-DC switching power supplies, DC-DC power converters, high voltage H-bridge motor drive PWM.


Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DSS}	Drain Source Voltage	500	V
I_D	Continuous Drain Current (@ $T_c=25^\circ\text{C}$)	18	A
	Continuous Drain Current (@ $T_c=100^\circ\text{C}$)	12.7	A
I_{DM}	Drain Current Pulsed (Note1)	80	A
V_{GS}	Gate to Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note2)	330	mJ
E_{AR}	Repetitive Avalanche Energy (Note1)	27.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	4.5	V/ns
P_D	Total Power Dissipation (@ $T_c=25^\circ\text{C}$)	208	W
	Derating Factor above 25°C	1.67	W/°C
T_J, T_{stg}	Junction and Storage Temperature	-55~150	°C
T_L	Channel Temperature	300	°C

Thermal Characteristics

Symbol	Parameter	Value			Units
		Min	Typ	Max	
R_{QJC}	Thermal Resistance, Junction-to-Case	-	-	0.6	°C/W
R_{QCS}	Thermal Resistance, Case-to-Sink	-	0.5	-	°C/W
R_{QJA}	Thermal Resistance, Junction-to-Ambient	-	-	62.5	°C/W

Electrical Characteristics(Tc=25℃)

Characteristics		Symbol	Test Condition	Min	Type	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} =±25V,V _{DS} =0V	-	-	±10	nA
Gate-source breakdown voltage		V _{(BR)GSS}	I _G =±10 μA,V _{DS} =0V	±30	-	-	V
Drain cut -off current		I _{DSS}	V _{DS} =500V,V _{GS} =0V	-	-	100	μA
Drain -source breakdown voltage		V _{(BR)DSS}	I _D =10 mA,V _{GS} =0V	500	-	-	V
Breakdown voltage Temperature coefficient		△BV _{DSS} / △T _J	I _D =250μA,Referenced to 25℃	-	0.5	-	V/℃
Gate threshold voltage		V _{GS(th)}	V _{DS} =10V,I _D =1mA	3	-	5	V
Drain -source ON resistance		R _{DS(ON)}	V _{GS} =10V,I _D =9A	-	0.235	0.27	Ω
Forward Transconductance		g _{fs}	V _{DS} =40V,I _D =9A	-	16	-	S
Input capacitance		C _{iss}	V _{DS} =25V,	-	2530	3290	pF
Reverse transfer capacitance		C _{rss}	V _{GS} =0V,	-	11	14.3	
Output capacitance		C _{oss}	f=1MHz	-	300	390	
Switching time	Rise time	tr	V _{DD} =250V,	-	40	90	ns
	Turn-on time	ton	I _D =18A	-	150	310	
	Fall time	tf	R _G =25Ω	-	95	200	
	Turn-off time	toff	(Note4,5)	-	110	230	
Total gate charge(gate-source plus gate-drain)		Qg	V _{DD} =400V, V _{GS} =10V,	-	42	55	nC
Gate-source charge		Qgs	I _D =18A	-	12	-	
Gate-drain("miller") Charge		Qgd	(Note4,5)	-	14	-	

Source-Drain Ratings and Characteristics(Ta=25℃)

Characteristics	Symbol	Test Condition	Min	Type	Max	Unit
Continuous drain reverse current	I_{DR}	-	-	-	18	A
Pulse drain reverse current	I_{DRP}	-	-	-	72	A
Forward voltage(diode)	V_{DSF}	$I_{DR}=18A, V_{GS}=0V$	-	-	1.4	V
Reverse recovery time	t_{rr}	$I_{DR}=18A, V_{GS}=0V,$	-	500	-	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt=100 A/\mu s$	-	5.4	-	μC

Note 1.Repeativity rating :pulse width limited by junction temperature

2.L=5.2mH $I_{AS}=18A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^\circ C$

3. $I_{SD}\leq 18A, di/dt\leq 200A/\mu s, V_{DD}<BV_{DSS}$, STARTING $T_J=25^\circ C$

4.Pulse Test:Pulse Width $\leq 300\mu s$, Duty Cycles $\leq 2\%$

5. Essentially independent of operating temperature.

This transistor is an electrostatic sensitive device

Please handle with caution

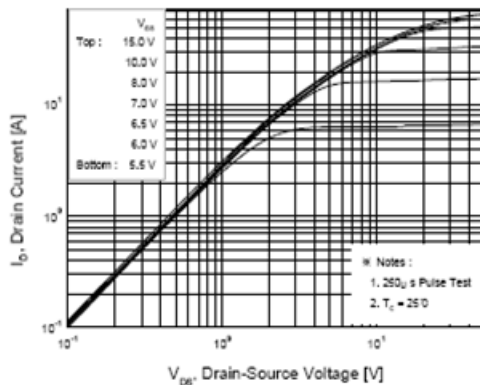


Fig.1 On State Characteristics

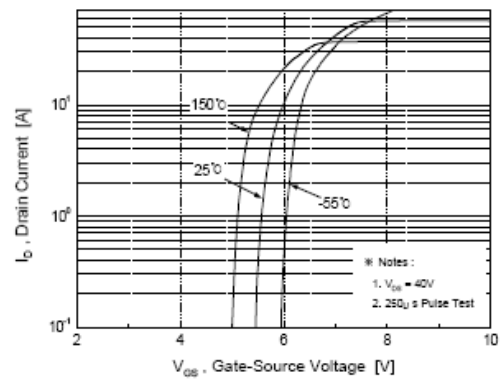


Fig.2 Transfer Current Characteristics

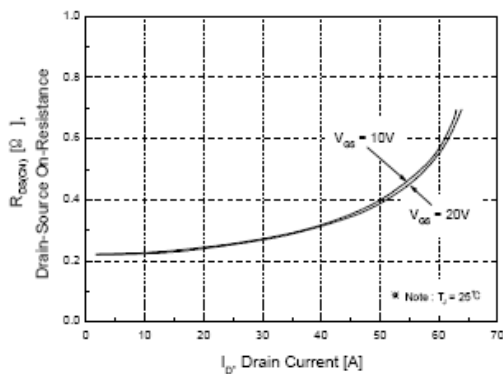


Fig.3 On-Resistance Variation vs Drain Current

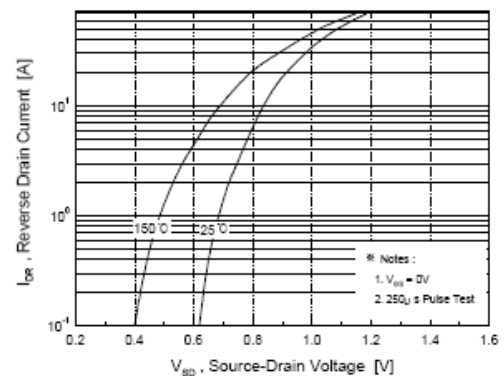


Fig.4 Body Diode Forward Voltage Variation with Source Current and Temperature

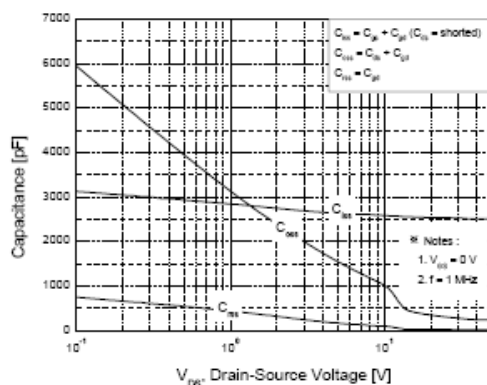


Fig.5 Capacitance Characteristics

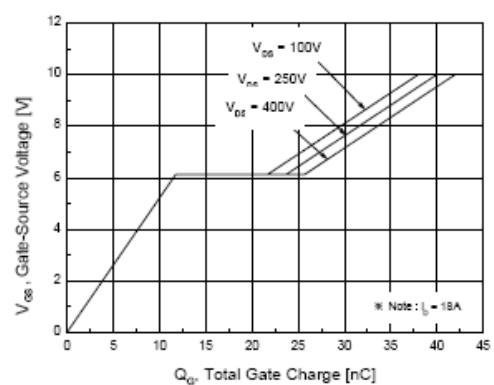
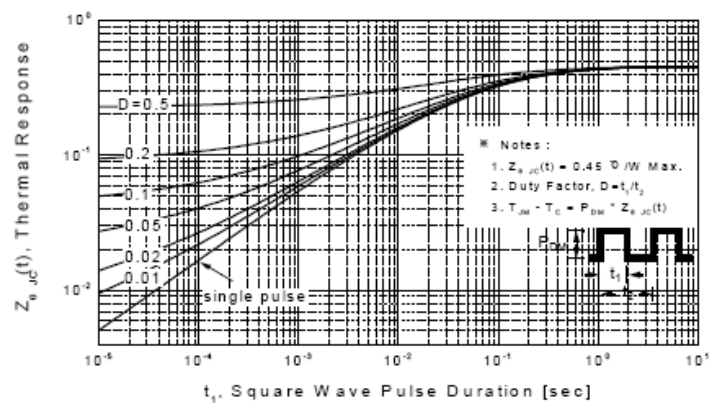
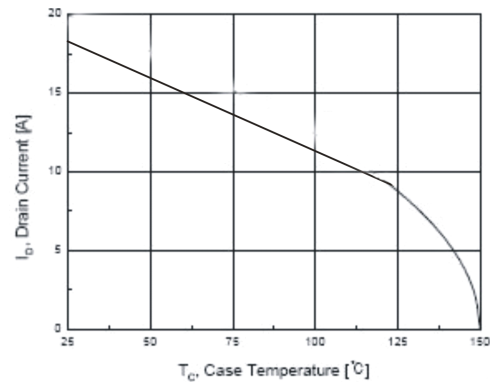
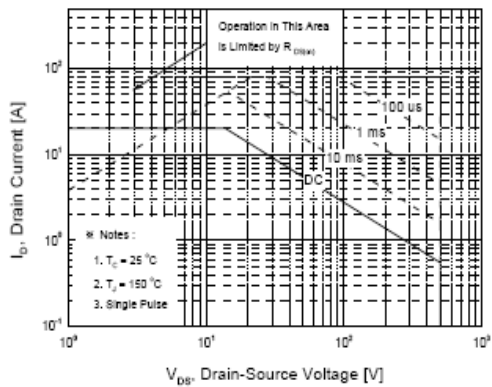
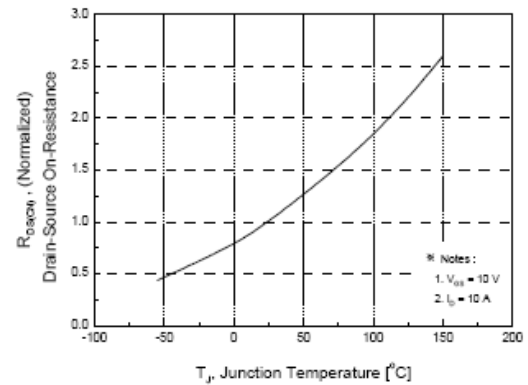
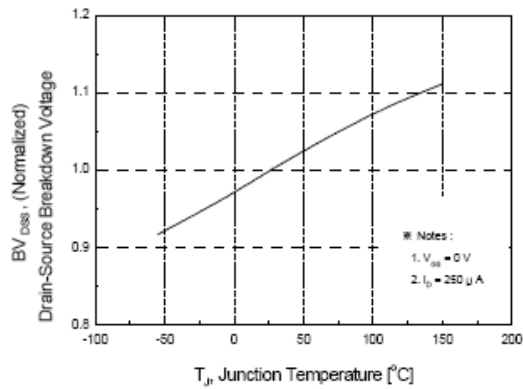


Fig.6 Gate Charge Characteristics



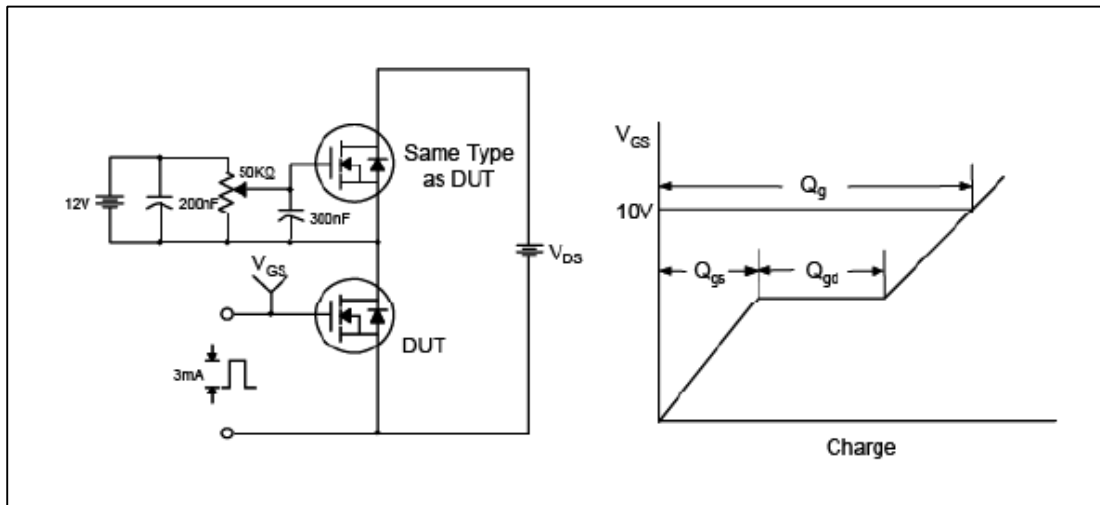


Fig.12 Gate Test Circuit & Waveform

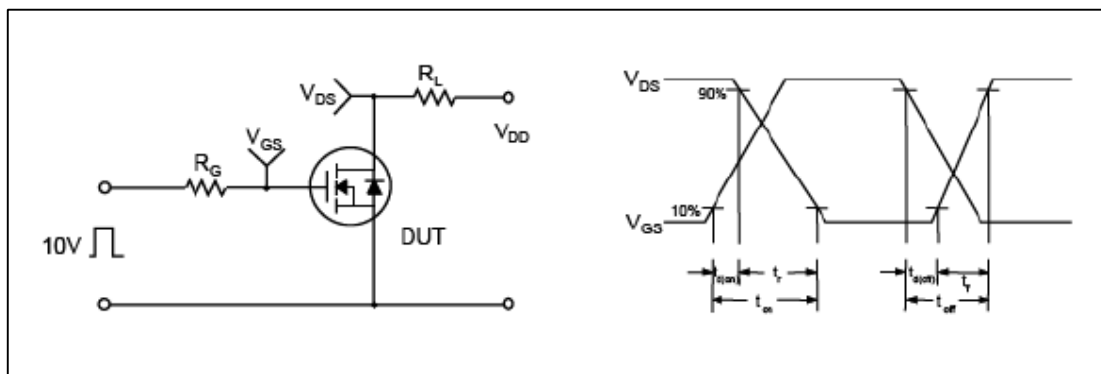


Fig.13 Resistive Switching Test Circuit & Waveform

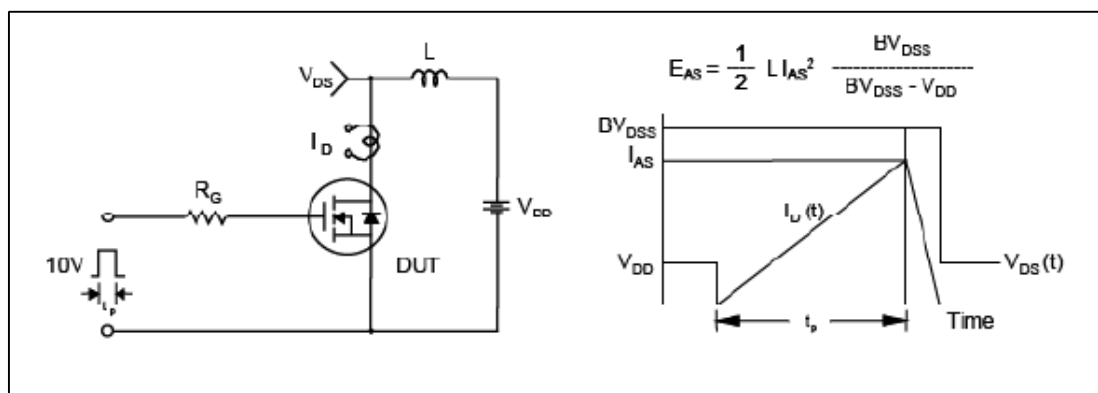


Fig.14 Unclamped Inductive Switching Test Circuit & Waveform



Technical drawing of a 3-pin connector showing front, side, and top views with dimensions in millimeters.

Front View Dimensions:

- Overall width: 9.90 ± 0.20
- Internal width: (8.70)
- Top pin diameter: $\phi 3.60 \pm 0.10$
- Top pin height: 1.30 ± 0.10
- Top pin offset: (1.70)
- Top pin width: 2.80 ± 0.10
- Top pin offset: (3.70)
- Top pin width: (3.00)
- Top pin offset: (1.46)
- Top pin width: 15.90 ± 0.20
- Top pin offset: 18.95 MAX.
- Top pin width: 10.08 ± 0.30
- Top pin offset: (1.00)
- Top pin width: 1.27 ± 0.10
- Top pin offset: (1.00)
- Top pin width: 1.52 ± 0.10
- Top pin offset: (1.00)
- Top pin width: 0.80 ± 0.10
- Top pin offset: (1.00)
- Top pin width: 2.54 TYP
- Top pin offset: $[2.54 \pm 0.20]$
- Top pin width: 2.54 TYP
- Top pin offset: $[2.54 \pm 0.20]$

Side View Dimensions:

- Overall height: 4.50 ± 0.20
- Top pin height: $1.30^{+0.10}_{-0.05}$
- Top pin offset: $0.50^{+0.10}_{-0.05}$
- Top pin width: 2.40 ± 0.20

Top View Dimensions:

- Overall width: 10.00 ± 0.20